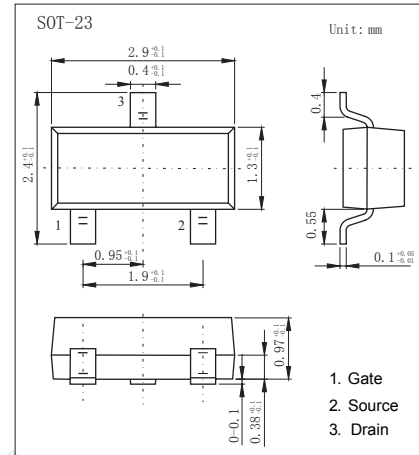
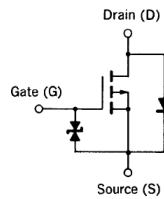


P-Channel MOSFET

2SJ211

Features

- $V_{DS} (V) = -100V$
- $I_D = -0.2 A$
- $R_{DS(ON)} < 20 \Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 30 \Omega$ ($V_{GS} = -4V$)



Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-0.2	A
Pulsed Drain Current (Note.1)	I_{DM}	-0.4	
Power Dissipation	P_D	0.2	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10$ ms, duty cycle $\leq 50\%$

Electrical Characteristics $T_a = 25^\circ C$

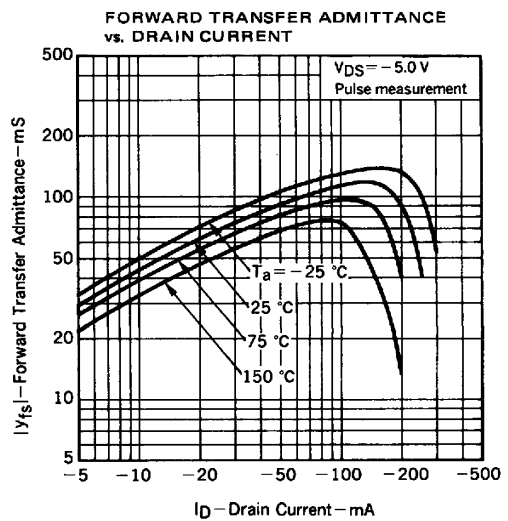
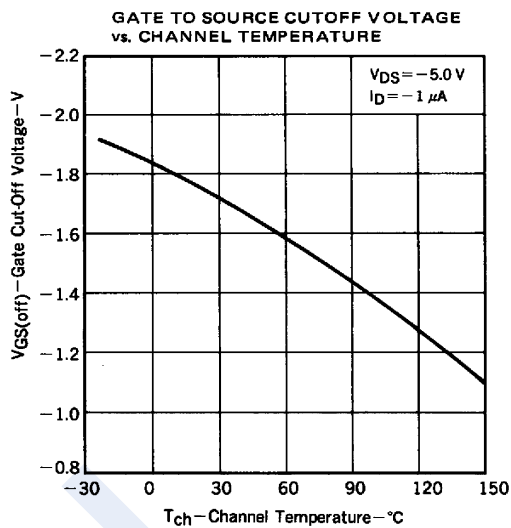
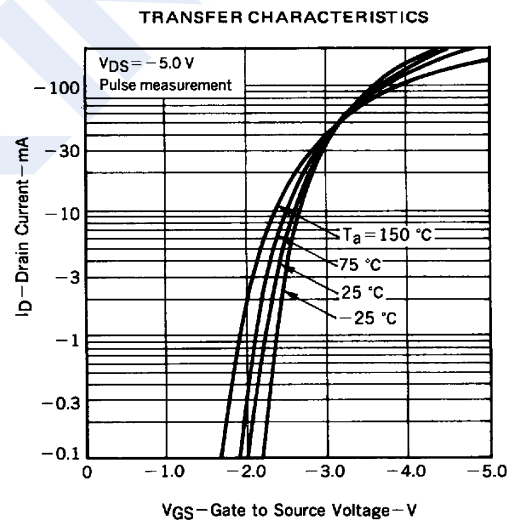
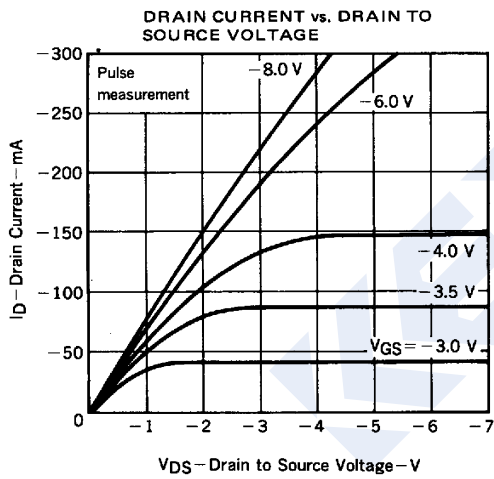
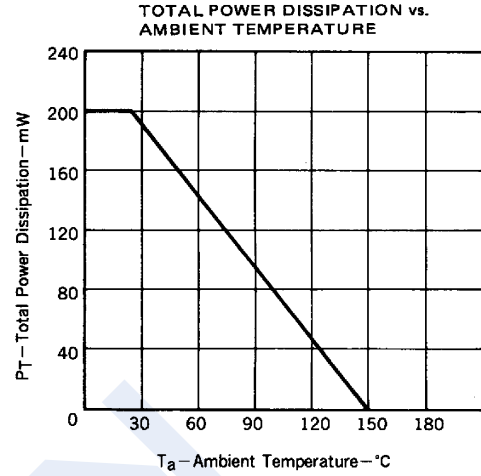
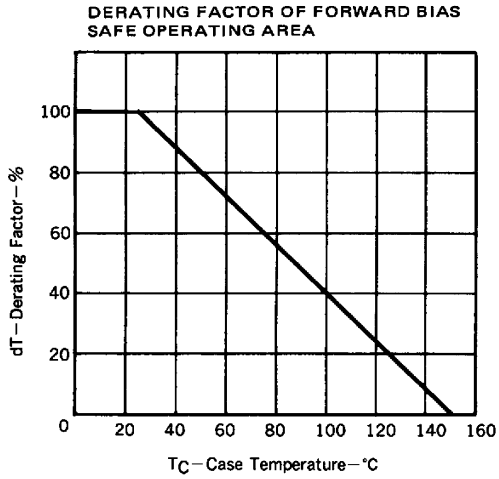
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{BSS}	$I_D = -250 \mu A, V_{GS} = 0V$	-100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100V, V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 10	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -5V, I_D = -1mA$	-1.4		-2.4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -10mA$			20	Ω
		$V_{GS} = -4V, I_D = -10mA$			30	
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -10mA$	20	45		mS
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -5V, f = 1MHz$		27		pF
Output Capacitance	C_{oss}			16		
Reverse Transfer Capacitance	C_{rss}			2		
Turn-On Delay Time	$t_{d(on)}$				110	
Turn-On Rise Time	t_r	$V_{GS(on)} = -4V, I_D = -10mA,$ $R_L = 500 \Omega, R_G = 10 \Omega, V_{DD} = -5V,$		150		
Turn-Off Delay Time	$t_{d(off)}$			160		
Turn-Off Fall Time	t_f			150		

Marking

Marking	H18
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P-Channel MOSFET 2SJ211

■ Typical Characteristics



P-Channel MOSFET 2SJ211

■ Typical Characteristics

